

Title (en)

METHOD FOR PRODUCING A CRYSTALLINE LAYER IN A III-N COMPOUND BY VAN DER WAALS EPITAXY FROM GRAPHENE

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER KRISTALLINEN SCHICHT IN EINER III-N-VERBINDUNG DURCH VAN-DER-WAALS-EPITAXIE AUS GRAPHEN

Title (fr)

PROCEDE DE REALISATION D'UNE COUCHE CRISTALLINE EN UN COMPOSE III-N PAR EPITAXIE VAN DER WAALS A PARTIR DE GRAPHENE

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Application

EP 18752572 A 20180709

Priority

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Abstract (en)

[origin: WO2019012215A1] The invention relates to a method for manufacturing a layer of interest (3) in a III-N crystalline compound by epitaxy from a layer of graphene (2), characterised in that it comprises, prior to a phase of nucleation of the layer of interest (3), a step of thermal treatment of the layer of graphene (2) in which it is subjected to a first temperature (T₁) no lower than 1050°C and to a stream of ammonia.

IPC 8 full level

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CPC (source: EP US)

C23C 16/303 (2013.01 - US); **C30B 25/10** (2013.01 - US); **C30B 25/183** (2013.01 - EP US); **C30B 29/403** (2013.01 - EP US)

Citation (search report)

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